許健 老師

現職 資訊工程學系 教授級專業技術人員

學歷 University of Iowa -- 博士

教師研究成果資料明細

SCI、SSCI、A&HCI、EI、TSSCI期刊論文

1.游信強(Hsin-Chiang You)、曹世昌(Shyh-Chang Tsaur)、許健(Gene Sheu) ,2009-03, (已刊登)
Semiconductor Science and Technology 18卷1期:129頁~133頁
Simulation Details for the Electrical Field Distribution and Breakdown Voltage of 0.15μm Thin Film SOI Power Device

2.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2009-01, (已刊登)
Semiconductor Science and Technology 18卷1期:123頁~124頁
A High Performance 80V Smart LDMOS Power Device Based on Thin SOI Technology

3.郭宇鋒(Yufeng Guo)、王至剛(Zhigong Wang)、許健(Gene Sheu) ,2009-07, (已刊登)
2009 International Conference on Communications, Circuits and Systems (ICCCAS2009) 2009卷july期:611頁~613頁
Variaton of Lateral Thickness techniques in SOI Lateral High Voltage Transistors

4.楊紹明(Shao-Ming Yang)、許健(Gene Sheu) ,2009-, (已刊登)
The Ninth International Conference on Electronic Measurement & Instruments 4卷9期:594頁~597頁
Dependence of Breakdown Voltage on Drift Length and Linear Doping Gradients in SOI RESURF LDMOS Devices

5.郭宇峰(Yufeng Guo)、(Zhigong Wang)、許健(Gene Sheu) ,2009-, (已刊登)
Journal of Semiconductors 30卷11期:114006-1頁~114006-4頁
A Three-dimensional Breakdown Model of SOI Lateral Power Transistors with a Circular Layout

6.郭宇峰(Yufeng Guo)、(Zhigong Wang)、許健(Gene Sheu) ,2009-11, (已刊登)
Journal of Semiconductors 30卷11期:114006-1頁~114006-4頁
A Three-dimensional Breakdown Model of SOI Lateral Power Transistors with a Circular Layout

7.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2010-02, (已刊登)
ECS Transactions 27卷1期:125頁~129頁
Combining 2D and 3D Device Simulations for Optimizing LDMOS Design

8.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2010-03, (已刊登)
ECS Transactions 27卷1期:125頁~129頁
Combining 2D and 3D Device Simulations for Optimizing LDMOS Design

9.郭宇?(GUO Yu-Feng)、王志功(WANG Zhi-Gong)、許健(Gene Sheu) ,2010-, (已刊登)
CHINESE PHYSICS LETTERS 27卷6期:067301-1頁~067301-4頁
A High Performance Silicon-on-Insulator LDMOSTT Using Linearly Increasing Thickness Techniques

10.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2010-07, (已刊登)
JAPANESE JOURNAL OF APPLIED PHYSICS 49卷2010期:074301-1頁~074301-8頁
An Analytical Model of Surface Electric Field Distributionsin in Ultrahigh-Voltage Metal–Oxide–Semiconductor Devices

11.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2010-02, (已刊登)
ECS Transactions 27卷1期:115頁~120頁
Reduction of Kink Effect in SOI LDMOS Structure with Linear Drift Region Thickness

12.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2010-03, (已刊登)
ECS Transactions 27卷1期:115頁~120頁
Reduction of Kink Effect in SOI LDMOS Structure with Linear Drift Region Thickness

13.許健(Gene Sheu)、楊紹明(Shao-Ming Yang)、陳兆南 ,2010-02, (已刊登)
ECS Transactions 27卷1期:103頁~108頁
Comparison of High Voltage (200-300 Volts) Lateral Power MOSFETs for Power Integrated Circuits

14.許健(Gene Sheu)、楊紹明(Shao-Ming Yang)、陳兆南 ,2010-03, (已刊登)
ECS Transactions 27卷1期:103頁~108頁
Comparison of High Voltage (200-300 Volts) Lateral Power MOSFETs for Power Integrated Circuits

15.許健(Gene Sheu)、楊紹明(Shao-Ming Yang)*、張怡楓(Yi-Fong Chang)、曹世昌(Shyh-Chang Tsaur) ,2010-07, (已刊登)
JAPANESE JOURNAL OF APPLIED PHYSICS 卷49期:74301頁~74308頁
An Analytical Model of Surface Electric Field Distributions in Ultrahigh-Voltage Buried P-top Lateral Diffused Metal-Oxide-Semiconductor Devices

16.楊紹明(Shao-Ming Yang)、許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai) ,2010-11, (已刊登)
ICSICT-2006: 2006 8th International Conference on Solid-State and Integrated Circuit Technology, Proceedings 1卷3期:1838頁~1840頁
A 5V/200V SOI Device with a Vertically Linear Graded Drift Region

17.許健(Gene Sheu) ,2011-, (已刊登)
ECS Transactions 34卷1期:979頁~984頁
LDMOS Thermal SOA Investigation of a Novel 800V Multiple RESURF with

18.許健(Gene Sheu) ,2010-11, ()
ICSICT-2006: 2006 8th International Conference on Solid-State and Integrated Circuit Technology, Proceedings 2010卷2010期:1850頁~1852頁
A 2D Analytical Model of Bulk-silicon Triple RESURF Devices

19.許健(Gene Sheu) ,2010-11, (已刊登)
ICSICT-2006: 2006 8th International Conference on Solid-State and Integrated Circuit Technology, Proceedings 2010卷期:1850頁~1852頁

A 2D Analytical Model of Bulk-silicon Triple RESURF Devices

20.許健(Gene Sheu)、楊紹明(Shao-Ming Yang)、曹世昌(Shyh-Chang Tsaur) ,2009-, ()
SEMICONDUCTOR SCIENCE AND TECHNOLOGY 卷期:頁~頁
An Analytical Model for Surface Electric Field Distributions in Ultra High Voltage (800V) Buried P-top LDMOS Devices

21.許健(Gene Sheu)、楊紹明(Shao-Ming Yang)、曹世昌(Shyh-Chang Tsaur) ,2009-, ()
SEMICONDUCTOR SCIENCE AND TECHNOLOGY 卷期:頁~頁
Comparison of High Voltage (200-300 Volts) Devices for Power Integrated Circuits

22.楊紹明(Shao-Ming Yang)、許健(Gene Sheu) ,2009-, ()
APPLIED PHYSICS LETTERS 卷期:頁~頁
The Reliability of 200V P-channel Silicon-On-Insulator LDMOS on High Side operation

23.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2009-03, (已刊登)
ECS Transactions 18卷期:123頁~128頁
A High Performance 80V Smart LDMOS Power Device Based on Thin SOI Technology

24.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2010-11, ()
IEEE Region 10 Annual International Conference, Proceedings/TENCON 卷2010期:71頁~74頁
An 800 Volts High Voltage Interconnection Level Shifter Using Floating Poly Field Plate (FPFP) Method

25.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2010-11, (已刊登)
IEEE Region 10 Annual International Conference, Proceedings/TENCON 卷1期:71頁~74頁
An 800 Volts High Voltage Interconnection Level Shifter Using Floating Poly Field Plate (FPFP) Method

26.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2010-11, ()
IEEE Region 10 Annual International Conference, Proceedings/TENCON 2010卷2010期:75頁~79頁
A Novel 800V Multiple RESURF LDMOS Utilizing Linear P-top Rings

27.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2010-11, (已刊登)
IEEE Region 10 Annual International Conference, Proceedings/TENCON 卷1期:75頁~79頁
A Novel 800V Multiple RESURF LDMOS Utilizing Linear P-top Rings

28.許健(Gene Sheu)、楊紹明(Shao-Ming Yang) ,2010-10, (已刊登)
IEEE Region 10 Annual International Conference, Proceedings/TENCON 卷1期:80頁~83頁
ESD Simulation on GGNMOS for 40V BCD

29.楊紹明(Shao-Ming Yang)、許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai) ,2011-08, (已刊登)
ICEMI 1卷期:85頁~88頁
Application of Multi-Lateral Double Diffused Field Ring in Ultrahigh-Voltage Device MOS Transistor Design

30.蔡宗叡(Jung-Ruey Tsai)、許健(Gene Sheu)、楊紹明(Shao-Ming

Yang) ,2011-08, (已刊登)
ICEMI 1卷期:235頁~238頁
Analysis of Si3N4 passivation effect by self-consistent electro-thermal-mechanical simulation in AlGaN/GaN heterostructure HEMTs

31.楊紹明(Shao-Ming Yang)、許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai) ,2011-08, (已刊登)
ICEMI 1卷期:239頁~242頁
Effects of SiO2 passivation on AlGaN/GaN HEMT by self-consistent electro-thermal-mechanical simulation

32.許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai)*、楊紹明(Shao-Ming Yang) ,2011-08, (已刊登)
The Ninth International Conference on Electronic Measurement & Instruments 4卷期:5頁~9頁
Improvement of Electrical Characteristics in LDMOS by the Insertion of PBL and Gate Extended Field Plate Technologies

33.許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai)*、楊紹明(Shao-Ming Yang) ,2011-08, (已刊登)
ICEMI 4卷期:5頁~9頁
Improvement of Electrical Characteristics in LDMOS by the Insertion of PBL